

MBR41H100CT, NRVBB41H100CT Series

SWITCHMODE Power Rectifier 100 V, 40 A

Features and Benefits

- Low Forward Voltage: 0.67 V @ 125°C
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 40 A Total (20 A Per Diode Leg)
- Guard-Ring for Stress Protection
- NRVBB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*
- MBR41H100CTH and MBRB41H100CT-1H are Halide-Free

Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

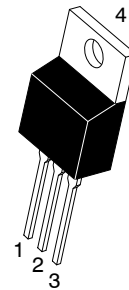
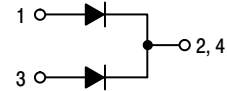
Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams (TO-220AB)
1.7 Grams (D²PAK)
1.5 Grams (TO-262)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes:
260°C Max. for 10 Seconds



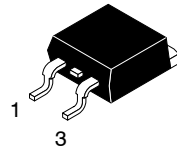
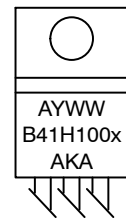
ON Semiconductor®

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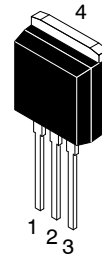
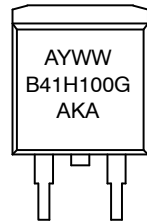


TO-220AB
CASE 221A
STYLE 6

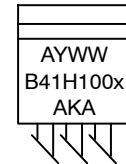
MARKING DIAGRAMS



D²PAK
CASE 418B
STYLE 3



I²PAK (TO-262)
CASE 418D
STYLE 3



A = Assembly Location
Y = Year
WW = Work Week
x = G or H
G = Pb-Free Package
H = Halide-Free Package
AKA = Polarity Designator

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR41H100CT, NRVBB41H100CT Series

MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current (Rated V_R) $T_C = 150^\circ\text{C}$	$I_{F(AV)}$	20	A
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz) $T_C = 145^\circ\text{C}$	I_{FRM}	40	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	350	A
Operating Junction Temperature (Note 1)	T_J	+175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +175	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/ μs
Controlled Avalanche Energy (see test conditions in Figures 10 and 11)	W_{AVAIL}	400	mJ
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance Junction-to-Case Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.0 70	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($I_F = 20\text{ A}$, $T_C = 25^\circ\text{C}$) ($I_F = 20\text{ A}$, $T_C = 125^\circ\text{C}$) ($I_F = 40\text{ A}$, $T_C = 25^\circ\text{C}$) ($I_F = 40\text{ A}$, $T_C = 125^\circ\text{C}$)	V_F	0.80 0.67 0.90 0.76	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 125^\circ\text{C}$) (Rated DC Voltage, $T_C = 25^\circ\text{C}$)	i_R	10 0.01	mA

- The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.
- Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

MBR41H100CT, NRVBB41H100CT Series

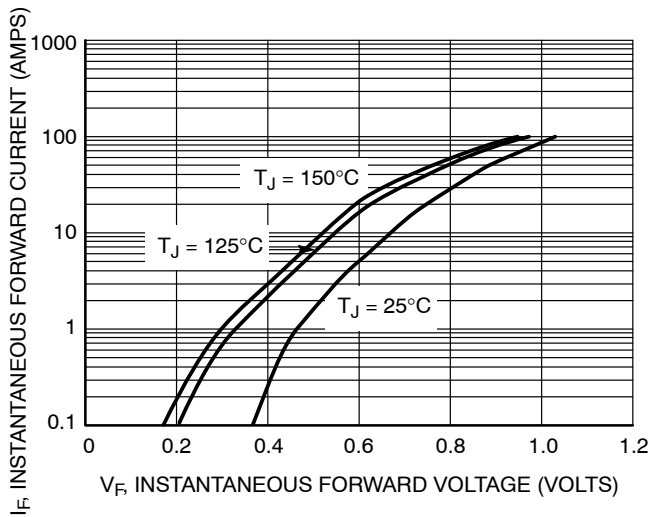


Figure 1. Typical Forward Voltage

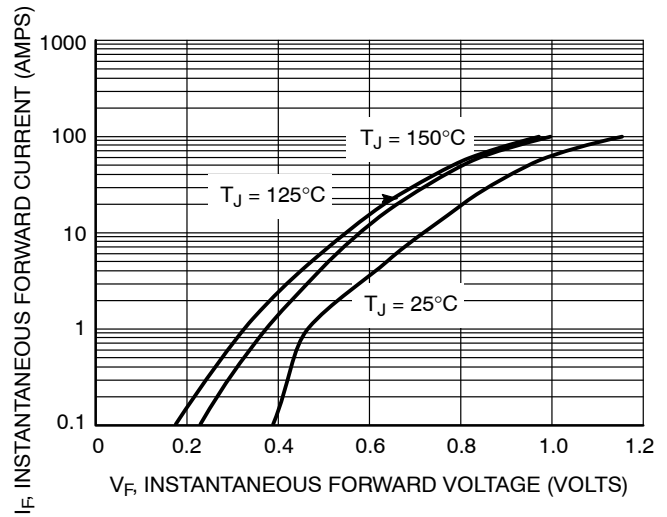


Figure 2. Maximum Forward Voltage

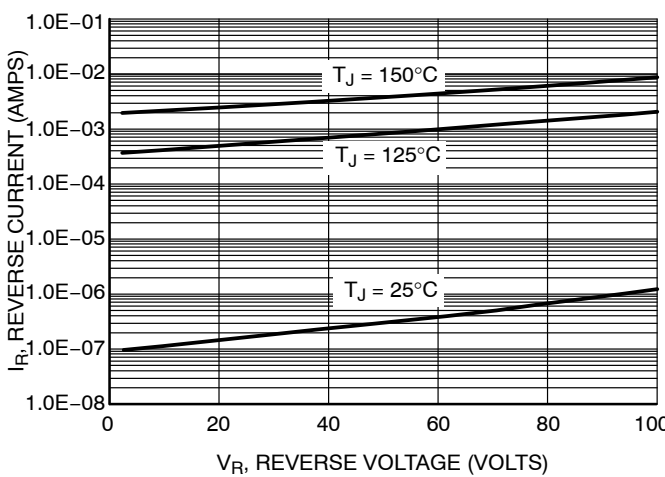


Figure 3. Typical Reverse Current

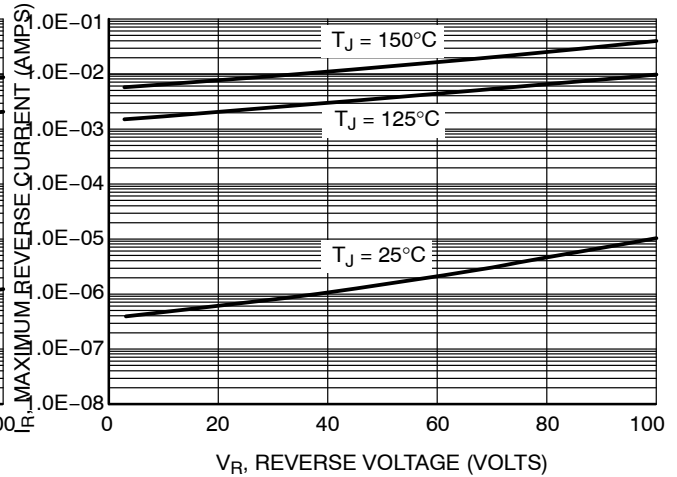


Figure 4. Maximum Reverse Current

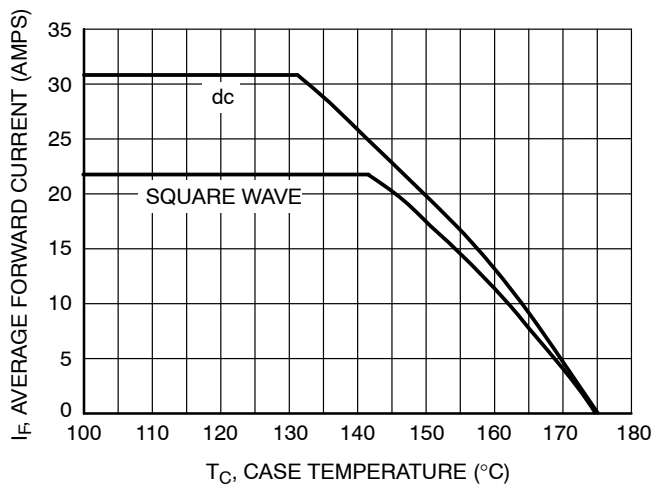


Figure 5. Current Derating

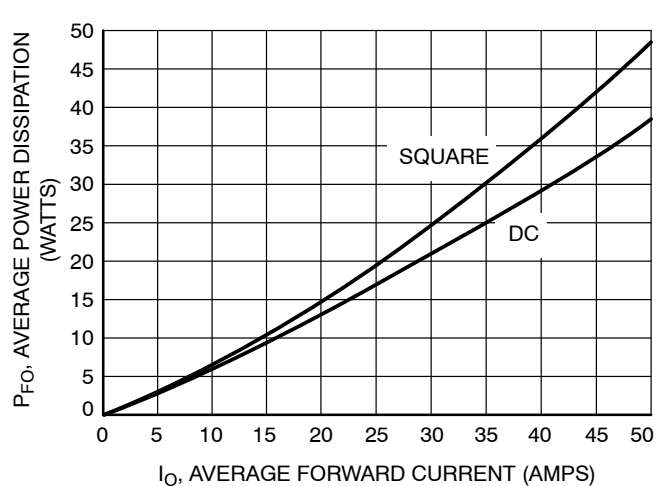


Figure 6. Forward Power Dissipation

MBR41H100CT, NRVBB41H100CT Series

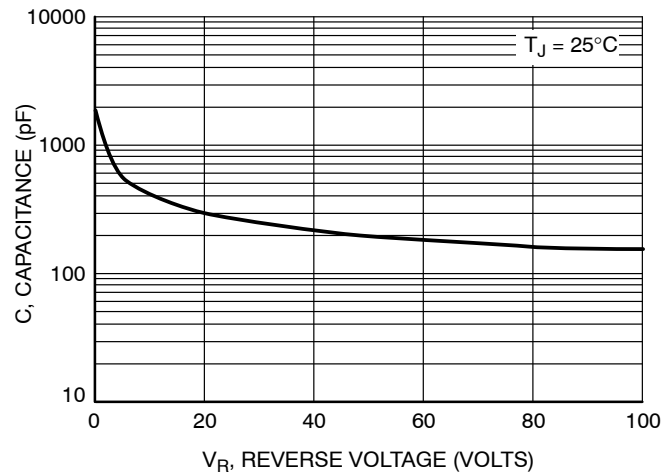


Figure 7. Capacitance

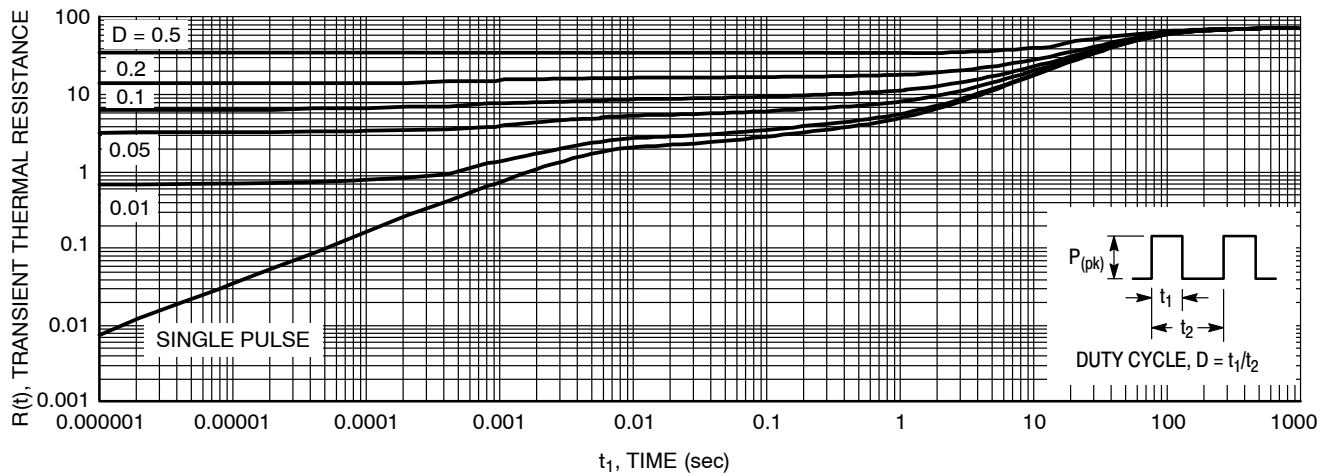


Figure 8. Thermal Response Junction-to-Ambient

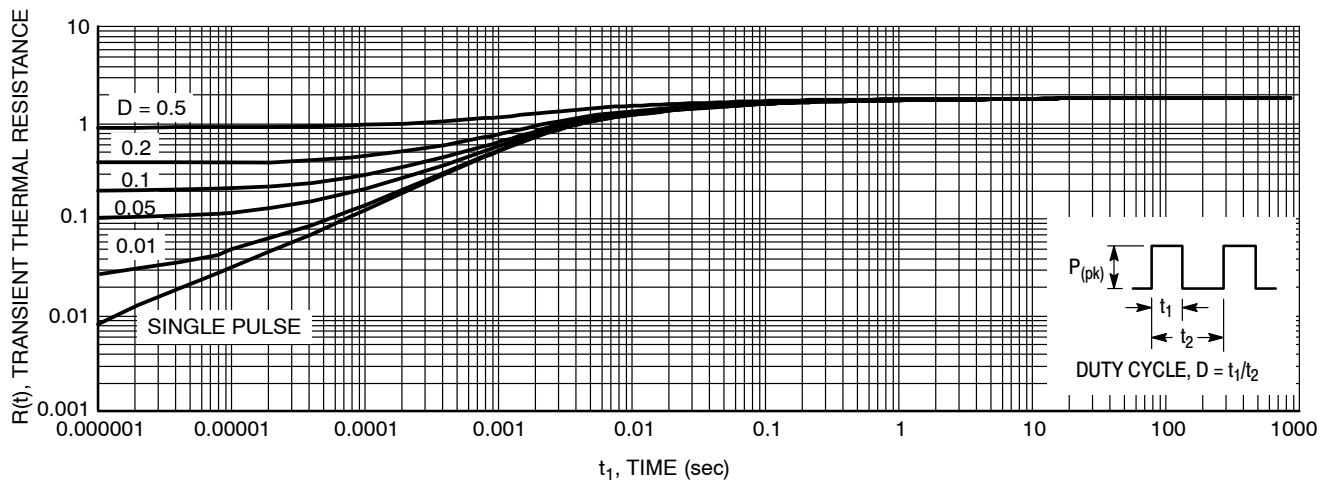


Figure 9. Thermal Response Junction-to-Case

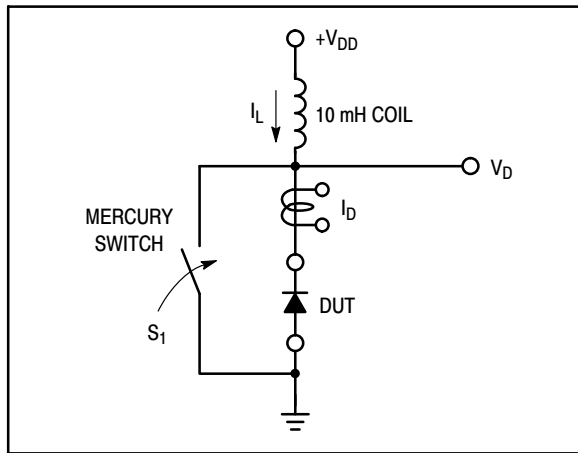


Figure 10. Test Circuit

The unclamped inductive switching circuit shown in Figure 10 was used to demonstrate the controlled avalanche capability of this device. A mercury switch was used instead of an electronic switch to simulate a noisy environment when the switch was being opened.

When S_1 is closed at t_0 the current in the inductor I_L ramps up linearly; and energy is stored in the coil. At t_1 the switch is opened and the voltage across the diode under test begins to rise rapidly, due to di/dt effects, when this induced voltage reaches the breakdown voltage of the diode, it is clamped at BV_{DUT} and the diode begins to conduct the full load current which now starts to decay linearly through the diode, and goes to zero at t_2 .

By solving the loop equation at the point in time when S_1 is opened; and calculating the energy that is transferred to the diode it can be shown that the total energy transferred is equal to the energy stored in the inductor plus a finite amount of energy from the V_{DD} power supply while the diode is in breakdown (from t_1 to t_2) minus any losses due to finite component resistances. Assuming the component resistive

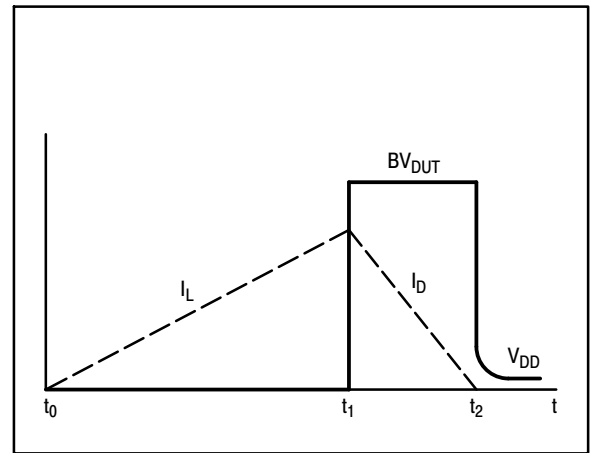


Figure 11. Current-Voltage Waveforms

elements are small Equation (1) approximates the total energy transferred to the diode. It can be seen from this equation that if the V_{DD} voltage is low compared to the breakdown voltage of the device, the amount of energy contributed by the supply during breakdown is small and the total energy can be assumed to be nearly equal to the energy stored in the coil during the time when S_1 was closed, Equation (2).

EQUATION (1):

$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^2 \left(\frac{BV_{DUT}}{BV_{DUT} - V_{DD}} \right)$$

EQUATION (2):

$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^2$$

MBR41H100CT, NRVBB41H100CT Series

ORDERING INFORMATION

Device	Package	Shipping†
MBR41H100CTG	TO-220AB (Pb-Free)	50 Units / Rail
MBR41H100CTH	TO-220AB (Halide-Free)	50 Units / Rail
MBRB41H100CT-1G	I ² PAK (Pb-Free)	50 Units / Rail
MBRB41H100CT-1H (In Development)	I ² PAK (Halide-Free)	50 Units / Rail
MBRB41H100CTT4G	D ² PAK (Pb-Free)	800 Units / Tape & Reel
NRVBB41H100CTT4G*	D ² PAK (Pb-Free)	800 Units / Tape & Reel

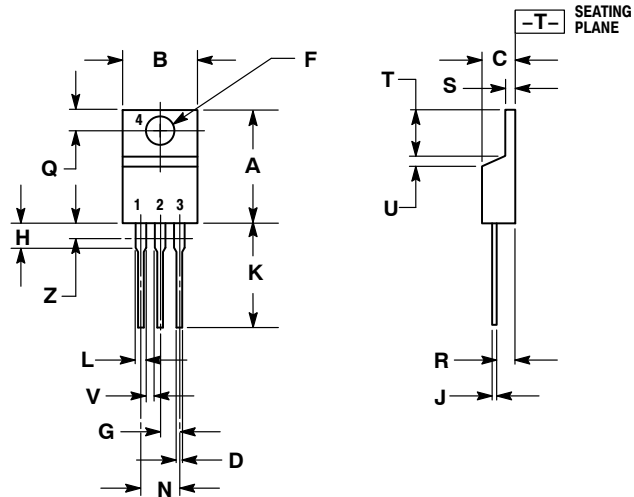
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NRVBB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MBR41H100CT, NRVBB41H100CT Series

PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AG



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 6:

- PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

PACKAGE DIMENSIONS

Technical drawing of a 4-pin connector, showing front and side views with dimensions and a feature control table.

Front View Dimensions:

- B-**: Width of the top flange.
- 4**: Number of pins.
- S**: Total height of the connector.
- 1, 2, 3**: Pin positions.
- T-**: Seating Plane.
- G**: Distance from the seating plane to the pin tip.
- D 3 PL**: Pin diameter and length.

Side View Dimensions:

- C**: Overall width.
- E**: Width of the top flange.
- V**: Distance from the top flange to the start of the main body.
- W**: Width of the main body.
- A**: Height of the main body.
- K**: Distance from the base to the start of the bend.
- J**: Distance from the base to the end of the bend.
- H**: Width of the base.

Feature Control Table:

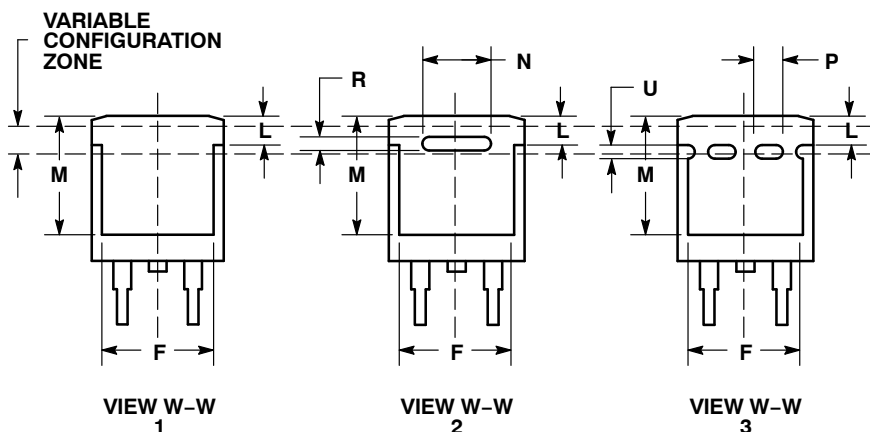
⌀	0.13 (0.005)	Ⓜ	T	B	Ⓜ
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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

PIN 1. ANODE
 2. CATHODE
 3. ANODE
 4. CATHODE



Technical drawing of a rectangular plate with the following dimensions and features:

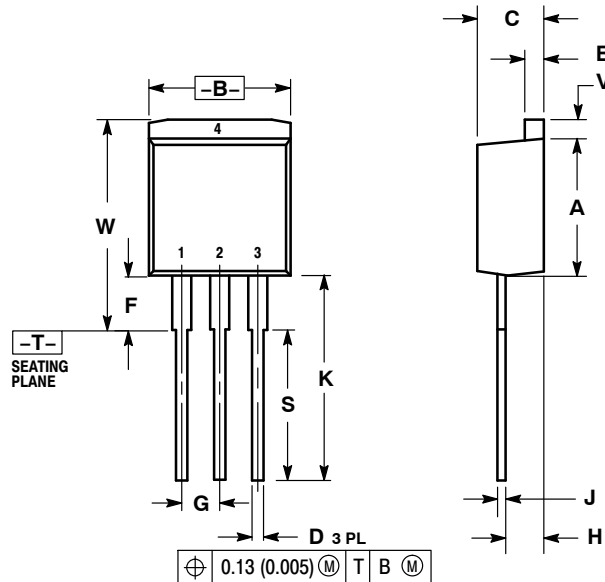
- Overall width: 10.49
- Overall height: 16.155
- Inner rectangular area width: 8.38
- Two mounting holes are shown, each with a diameter of $2X$.
- Distance from the bottom edge to the center of the mounting holes: 3.504
- Distance between the centers of the two mounting holes: 5.080 PITCH
- Distance from the left edge to the center of the first mounting hole: 1.016

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR41H100CT, NRVBB41H100CT Series

PACKAGE DIMENSIONS

I²PAK (TO-262) CASE 418D ISSUE D



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.335	0.380	8.51	9.65
B	0.380	0.406	9.65	10.31
C	0.160	0.185	4.06	4.70
D	0.026	0.035	0.66	0.89
E	0.045	0.055	1.14	1.40
F	0.122 REF		3.10 REF	
G	0.100 BSC		2.54 BSC	
H	0.094	0.110	2.39	2.79
J	0.013	0.025	0.33	0.64
K	0.500	0.562	12.70	14.27
S	0.390 REF		9.90 REF	
V	0.045	0.070	1.14	1.78
W	0.522	0.551	13.25	14.00

- STYLE 3:
- PIN 1. ANODE
 2. CATHODE
 3. ANODE
 4. CATHODE

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